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30V N-Channel MOSFET



PDFN56

Pin Definition:

Source
Source
Drain
Source
Drain

4. Gate 5. Drain

Note:

MSL 1 (Moisture Sensitivity Level) per J-STD-020

Key Parameter Performance

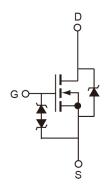
Parameter		Value	Unit	
V_{DS}		30	V	
R _{DS(on)} (max)	V _{GS} = 10V	5.5		
	$V_{GS} = 4.5V$	8.5	mΩ	
Q_g		11.1	nC	

Ordering Information

Part No.	Package	Packing		
TSM055N03EPQ56 RLG	PDFN56	2.5kpcs / 13" Reel		

Note: Halogen-free according to IEC 61249-2-21 definition

Block Diagram



N-Channel MOSFET with ESD protection

Absolute Maximum Ratings (Tc = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C = 25^{\circ}C$	- I _D	80	Α
	$T_C = 100$ °C		51	
Drain Current-Pulsed (Note 1)		I _{DM}	320	Α
Single Pulse Avalanche Energy (Note 2)		E _{AS}	45	mJ
Maximum Power Dissipation @ T _C = 25°C		P_{D}	74	W
Storage Temperature Range		T _{STG}	-55 to +150	$^{\circ}$
Operating Junction Temperature Range		T_J	-55 to +150	$^{\circ}$

Thermal Performance

Parameter	Symbol	Limit	Unit	
Thermal Resistance - Junction to Case	$R_{\Theta JC}$	1.7	°C/W	
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	62	°C/W	



30V N-Channel MOSFET



Electrical Specifications (T_C = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 20A$	R _{DS(ON)}		4.5	5.5	mΩ
	$V_{GS} = 4.5V, I_D = 10A$			6.3	8.5	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1.2	1.6	2.5	٧
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I _{DSS}			1	μΑ
	$V_{DS} = 24V, V_{GS} = 0V,$ $T_{J} = 125^{\circ}C$				10	μΑ
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±10	μΑ
Dynamic						
Total Gate Charge (Note 3,4)		Q_g		11.1		nC
Gate-Source Charge (Note 3,4)	$V_{DS} = 15V, I_{D} = 20A,$	Q_{gs}		1.85		
Gate-Drain Charge (Note 3,4)	$V_{GS} = 4.5V$	Q_{gd}		6.8		
Input Capacitance		C _{iss}		1210		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C _{oss}		190		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		100		1
Switching						
Turn-On Delay Time (Note 3,4)		t _{d(on)}		7.5		
Turn-On Rise Time (Note 3,4)	$V_{GS} = 10V, V_{DS} = 15V,$	t _r		14.5		
Turn-Off Delay Time (Note 3,4)	$R_G = 3.3\Omega, I_D = 15A$	t _{d(off)}		35.2		ns
Turn-Off Fall Time (Note 3,4)		t _f		9.6		
Drain-Source Diode Characteristic	s and Maximum Rating					
Maximum Continuous Drain-Source		ı			80	Α
Diode Forward Current	Integral reverse diode in the MOSFET	I _S			80	
Maximum Pulse Drain-Source		I _{SM}			320	Α
Diode Forward Current		· SIVI				
Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_{S} = 1A$	V_{SD}			1	V

Notes:

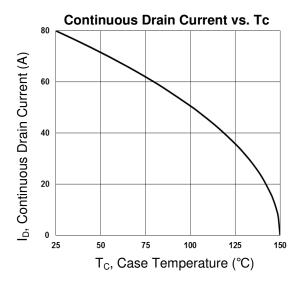
- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2. V_{DD} = 25V, V_{GS} = 10V, L = 0.1mH, I_{AS} = 42A, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C.
- 3. Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2%
- 4. Essentially independent of operating temperature.

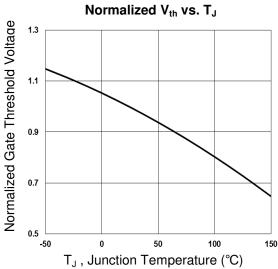


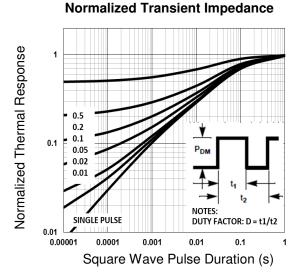
30V N-Channel MOSFET

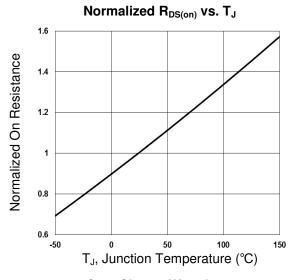
Pb ROHS COMPLIANT

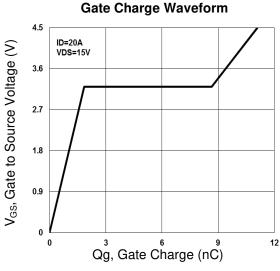
Electrical Characteristics Curves

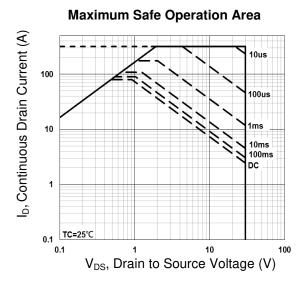










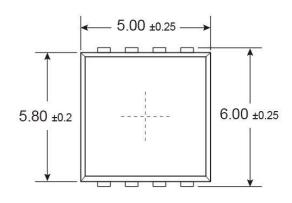


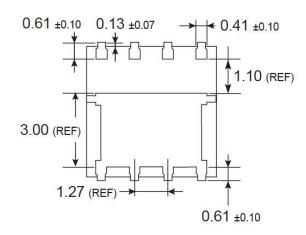


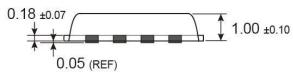
30V N-Channel MOSFET



PDFN56 Mechanical Drawing







Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

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L = Lot Code

Version: B1710



Pb ROHS

TSM055N03EPQ56 30V N-Channel MOSFET

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